

ZXMS6005SG

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

Continuous Drain Source Voltage V_{DS} = 60V
 On-State Resistance 200mΩ
 Nominal Load Current (V_{IN} = 5V) 2A
 Clamping Energy 480mJ

Description

The ZXMS6005SG is a self protected low side IntelliFETTM MOSFET with logic level input. It integrates over-temperature; over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6005SG is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially Suited for Loads with a High In-rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- μC Compatible Power Switch for 12V DC Applications
- Automotive Rated
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode capability the current-limiting protection circuitry is designed to de-activate at low V_{DS} to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}.

Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.
 - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMS6005SGQ)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.112 grams (Approximate)

SOT223 (Type DN)



Top View



S

S

D IN

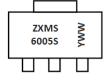
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXMS6005SGTA	ZXMS6005S	7	12	1,000 Units
ZXMS6005SG-13	ZXMS6005S	13	12	2,500 Units

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

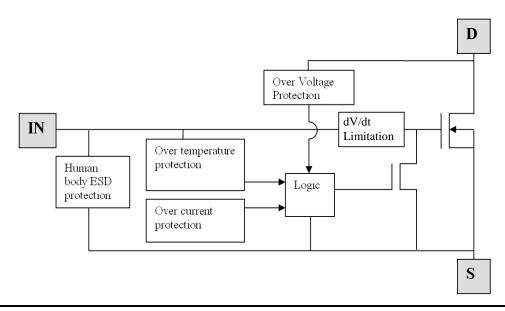
Marking Information



ZXMS6005S = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 0 = 2020) WW or $\overline{W}W$ = Week Code (01 to 53)



Functional Block Diagram



Absolute Maximum Ratings (@TA = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS} (SC)	24	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	lin	No limit I _{IN} ≤2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	5	Α
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	6	Α
Continuous Source Current (Body Diode) (Note 5)	Is	2.5	A
Pulsed Source Current (Body Diode)	Ism	10	Α
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	Eas	480	mJ
Electrostatic Discharge (Human Body Model)	Vesd	4000	V
Charged Device Model	V _{CDM}	1000	V

Thermal Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	1.0 8.0	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	PD	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	Reja	125	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	39	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Notes:

^{5.} For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

^{6.} For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

^{7.} Thermal resistance between junction and the mounting surfaces of drain and source pins.

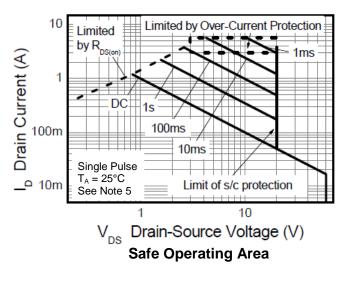


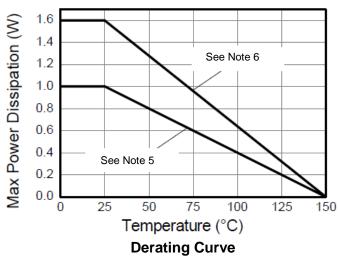
Recommended Operating Conditions

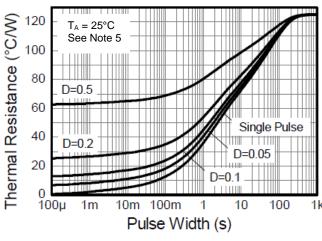
The ZXMS6005SG is optimized for use with μC operating from 3.3V and 5V supplies.

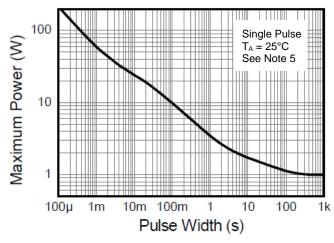
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	Vin	0	5.5	٧
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to Be On	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to Be Off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load Is Referred)	VP	0	24	V

Thermal Characteristics









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@TA = +25°C, unless otherwise stated.)

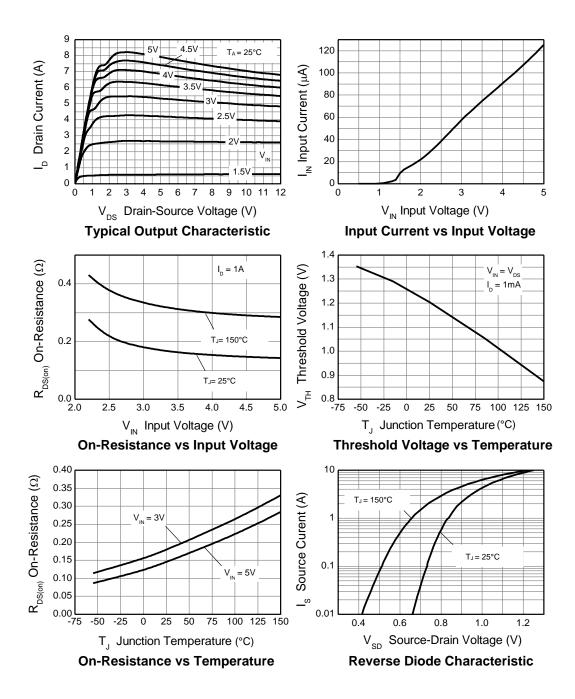
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics					•	·
Drain-Source Clamp Voltage	VDS(AZ)	60	65	70	V	I _D = 10mA
Off State Drain Current	1	_	_	1	μΑ	$V_{DS} = 12V, V_{IN} = 0V$
Oil State Drain Current	IDSS	_	_	2		V _{DS} = 36V, V _{IN} = 0V
Input Threshold Voltage	V _{IN(TH)}	0.7	1.2	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Input Current	lo.	1	60	100	μΑ	$V_{IN} = 3V$
Input Current	lin	1	120	200		$V_{IN} = 5V$
Input Current While Over Temperature Active		1	_	300	μA	V _{IN} = 5V
Static Drain-Source On-State Resistance	Dagger	1	170	250	mΩ	$V_{IN} = 3V$, $I_D = 1A$
Static Dialii-Source Oil-State Resistance	RDS(ON)	1	150	200	11122	$V_{IN} = 5V$, $I_D = 1A$
Continuous Drain Current (Note 5)		1.4	_	_		V _{IN} = 3V, T _A = +25°C
Continuous Diam Current (Note 3)	I _D	1.6	_	_	А	V _{IN} = 5V, T _A = +25°C
Continuous Drain Current (Note 6)		1.9	_	_		V _{IN} = 3V, T _A = +25°C
Continuous Diam Current (Note 6)		2.0	_	_		V _{IN} = 5V, T _A = +25°C
Current Limit (Note 8)	1	2.2	5	_	A	V _{IN} = 3V
Current Limit (Note 6)	I _{D(LIM)}	3.3	7	_		V _{IN} = 5V
Dynamic Characteristics						
Turn On Delay Time	t _{D(ON)}	l	6	_		
Rise Time	t _R	1	14	_		V _{DD} = 12V, I _D = 1A, V _{GS} = 5V
Turn Off Delay Time	tD(OFF)	1	34	_	μs	
Fall Time	t _F	-	19	_		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 9)	TJT	+150	+175	_	°C	_
Thermal Hysteresis (Note 9)	_	_	+10	_	°C	_

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
- 6. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
- 7. Thermal resistance between junction and the mounting surfaces of drain and source pins.
- 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
- 9. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

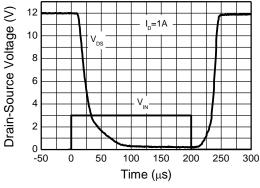


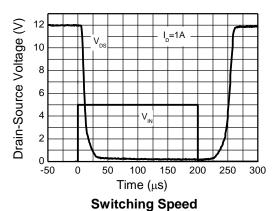
Typical Characteristics





Typical Characteristics (continued)





Switching Speed

W V_{IN} = 5V V_{DS} = 15V V_{DS}

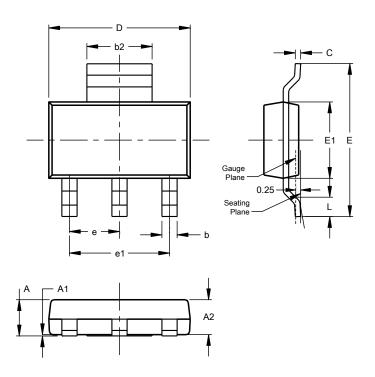
Typical Short Circuit Protection



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

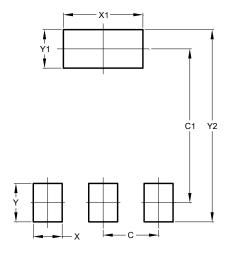


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15	-	
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32	-	
D	6.30	6.70		
Е	6.70	7.30	-	
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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